Sheet 1 of 1 FORM PTO-1449 SAMUELS, GAUTHIER & STEVENS LLP ATTORNEY DOCKET NO. MIT9888 SERIAL NO. Unknown 225 Franklin Street, Boston, MA 02110 (Rev. 5/92) Pitera et al. Telephone: (617) 426-9180 APPLICANT: GROUP: Unknown **Herewith** INFORMATION DISCLOSURE FILING DATE: **EXAMINER:** Unknown STATEMENT BY APPLICANT **U.S. PATENT DOCUMENTS** EXAMINER DOCUMENT FILING DATE INITIAL NUMBER DATE SUBCLASS IF APPROPRIATE NAME **CLASS** AA 5,882,987 3/16/99 Srikrishnan 8/26/97 AB 12/20/94 9/15/92 5,374,564 Bruel AC 6,573,126 6/3/03 8/10/01 Cheng et al. AD 6,475,072 11/5/02 Cama[ero et al. 9/29/00 AE 6,107,653 8/22/00 Fitzgerald 9/29/00 AF 11/21/00 9/30/98 6,150,239 Goesele et al. AG 3/31/97 5,877,070 3/2/99 Goesele et al. FOREIGN PATENT DOCUMENTS EXAMINER DOCUMENT TRANSLATION SUBCLASS INITIAL NUMBER DATE COUNTRY CLASS VES NO AΗ OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.) **EXAMINER** INITIAL "Silicon on Insulator Material Technology"; M. Bruel; Electronics Letters; July 6, 1995; Vol. 31, No. 14; AI pgs: 12011202 "Ge layer transfer to Si for photovoltaic applications"; Zahler et al., Thomas J. Watson Laboratory of **YX** Applied Physics, California Institute of Technology; pgs.: 558-562 "Transfer of 3 in GaAs film on silicon substrate by proton implantation process"; Jalaguier et al., Electronics Letters; February 19, 1998; Vol. 34, No. 4; pgs.: 408-409 AK "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on Insulator (SGOI) Substrates"; Cheng et al., IEEE Electron Device Letters; Vol. 22, No. 7, July 2001; pgs.: 321-323 "Preparation of Novel SiGe-Free Strained Si on Insulator Substrates"; Langdo et al., IEEE International AM SOI Conference; 2002; pgs.: 211-212 "Cleaning and Polishing As Key Steps For Smart-Cut SOI Process"; Moriceau et al., IEEE International AN SOI Conference, October 1996; pgs: 152-153 "Relaxed Silicon-Germanium on Insulator Substrate By La; yer Transfer"; Cheng et al., Journal of ΑO Electronic Materials; Vol. 30, No. 12; 2001; pgs.: L37-L39 DATE CONSIDERED **EXAMINER** Kester 09113104 Initial if citation considered, whether or not citati n is in c nf rmance with **EXAMINER:**

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